

SEMICONDUCTOR STRUCTURE WITH SUBSTANTIALLY ETCHED OXYNITRIDE DEFECTS...

Gary Chen et al.

Appl. No.: 10/614,538 Atty Docket: MICRON.109DC1D1



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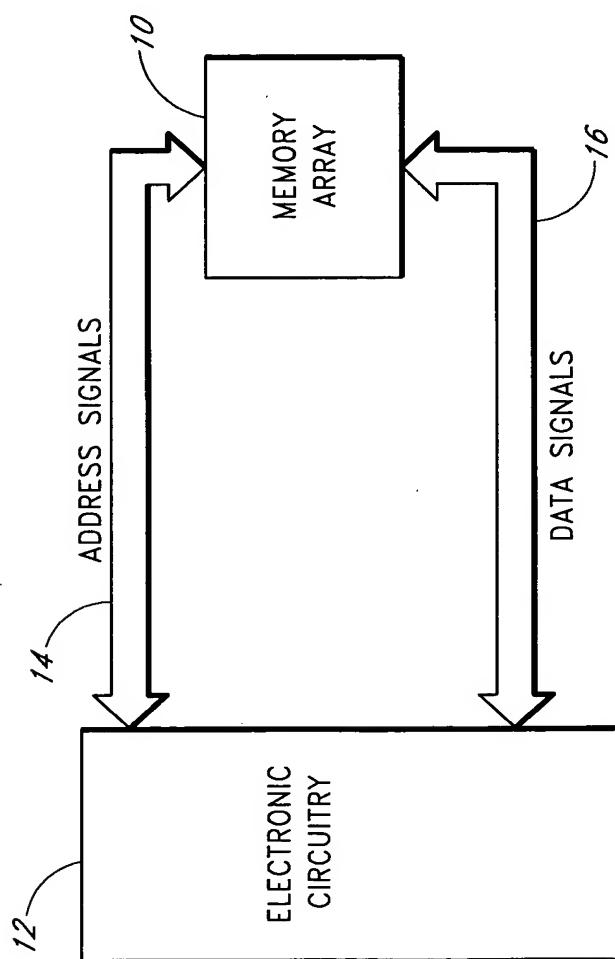


FIG. 1

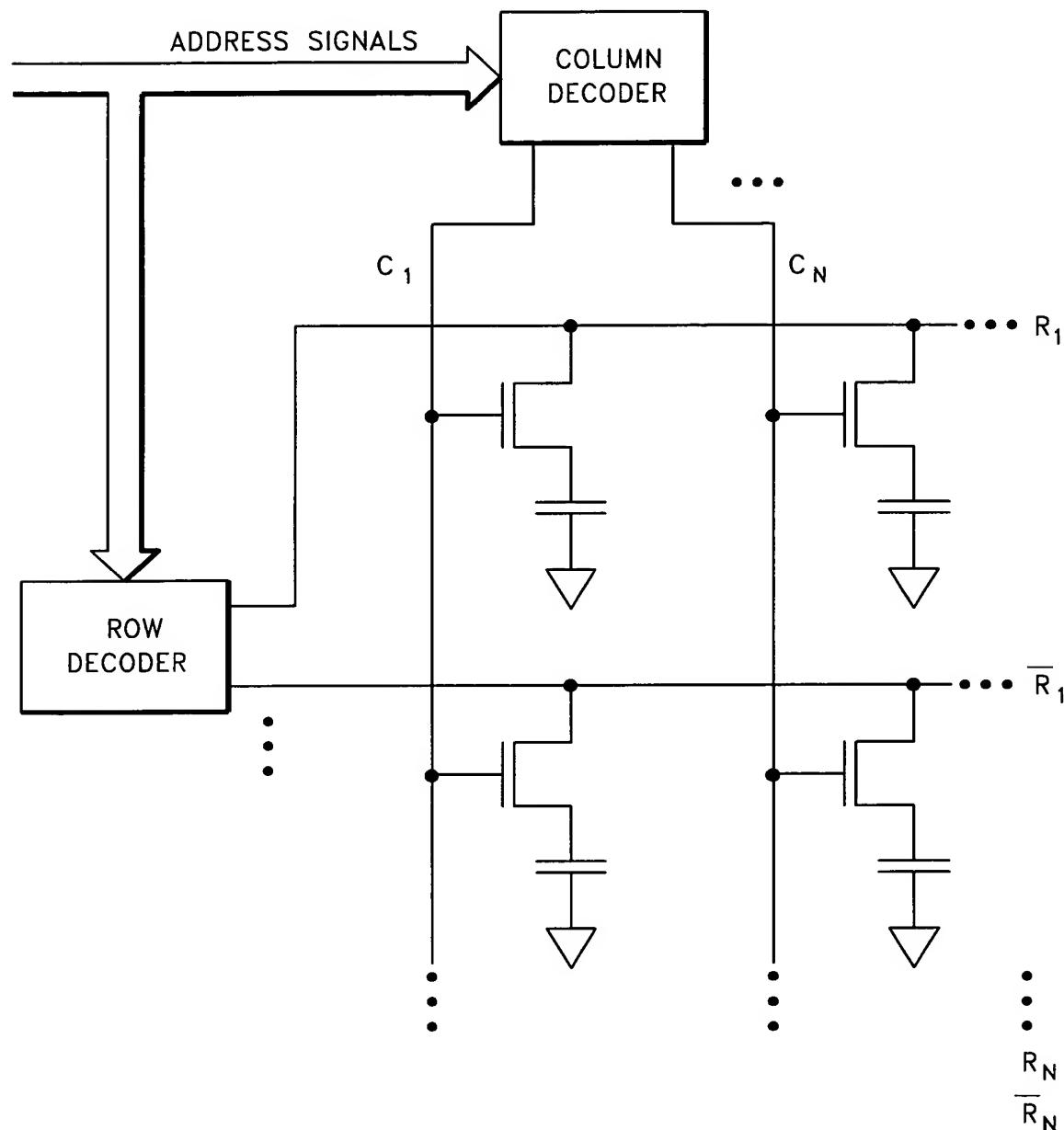


FIG. 2

SEMICONDUCTOR STRUCTURE WITH SUBSTANTIALLY ETCHED OXYNITRIDE DEFECTS...

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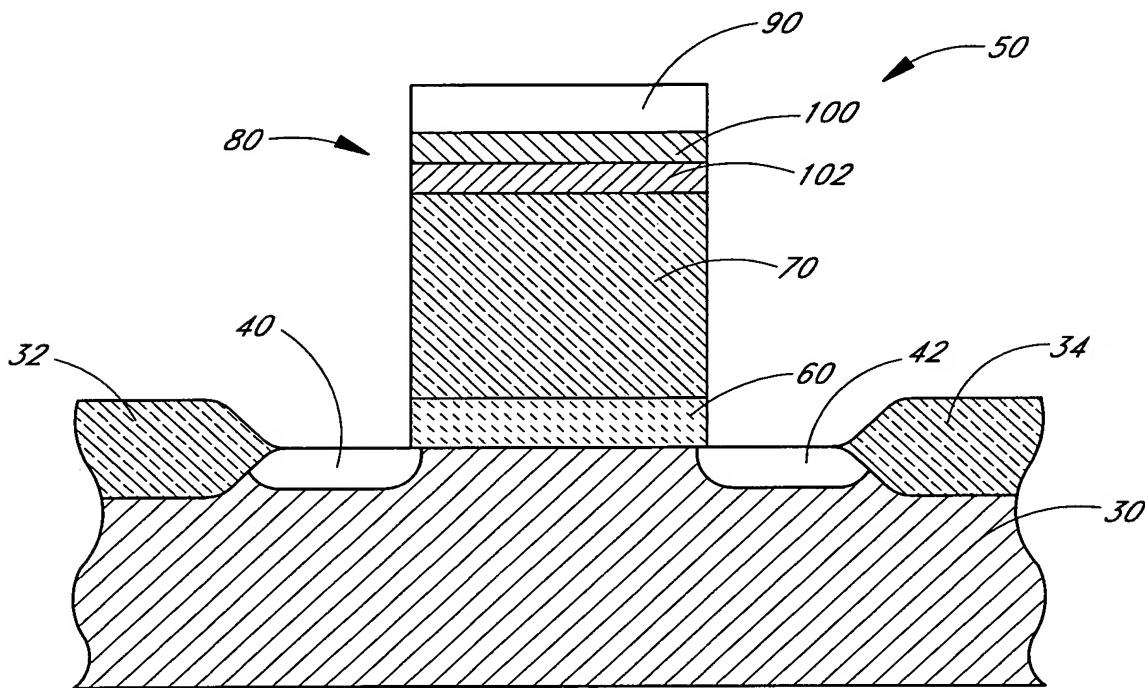


FIG. 3

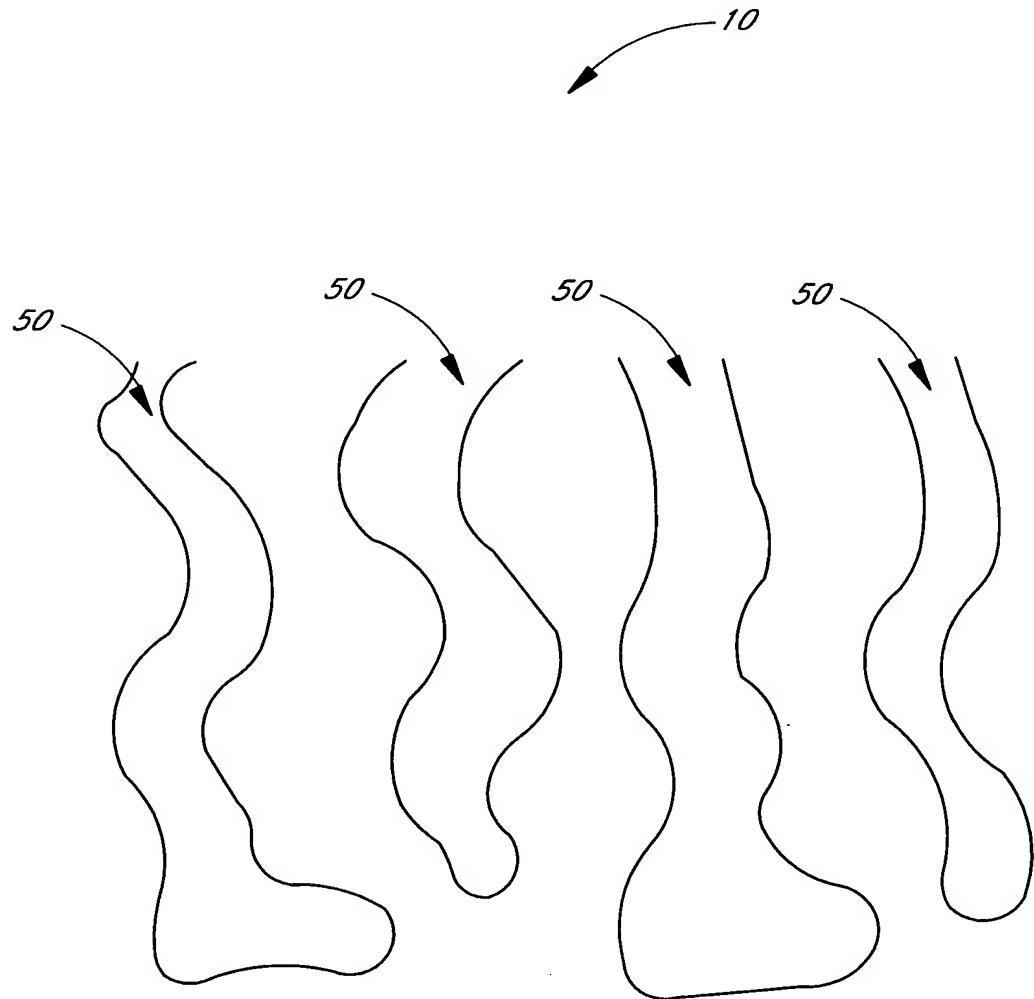


FIG. 4

SEMICONDUCTOR STRUCTURE WITH SUBSTANTIALLY ETCHED OXYNITRIDE DEFECTS...

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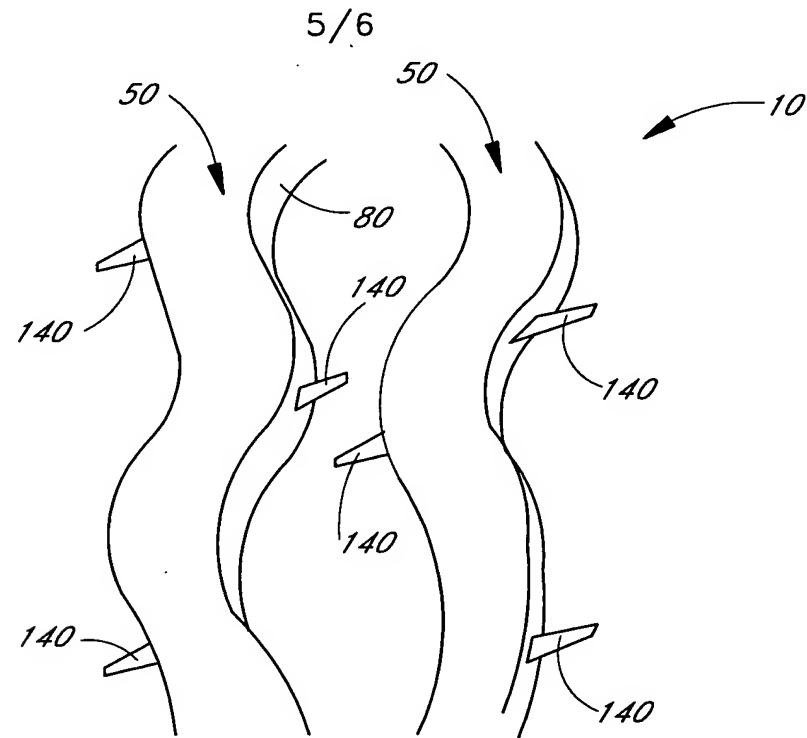


FIG. 5

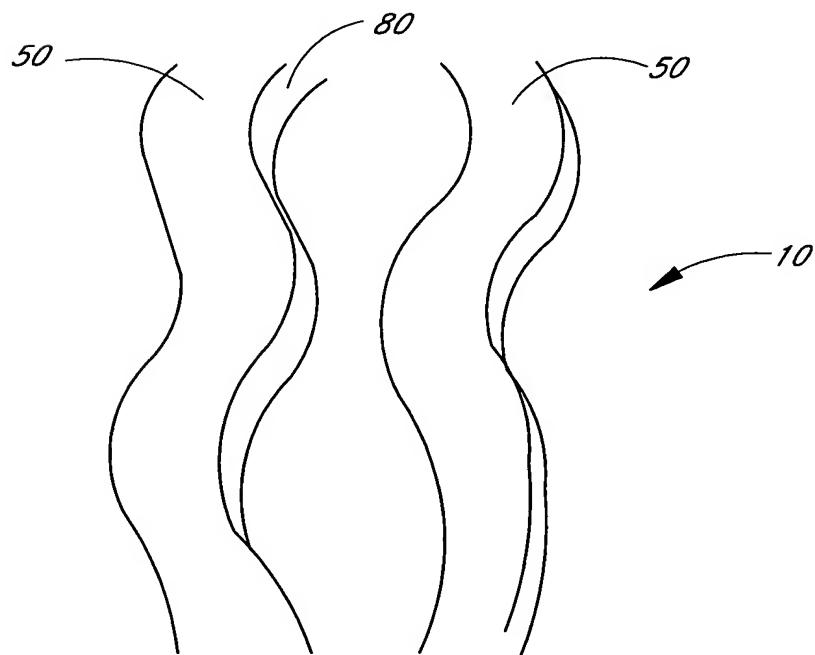


FIG. 6

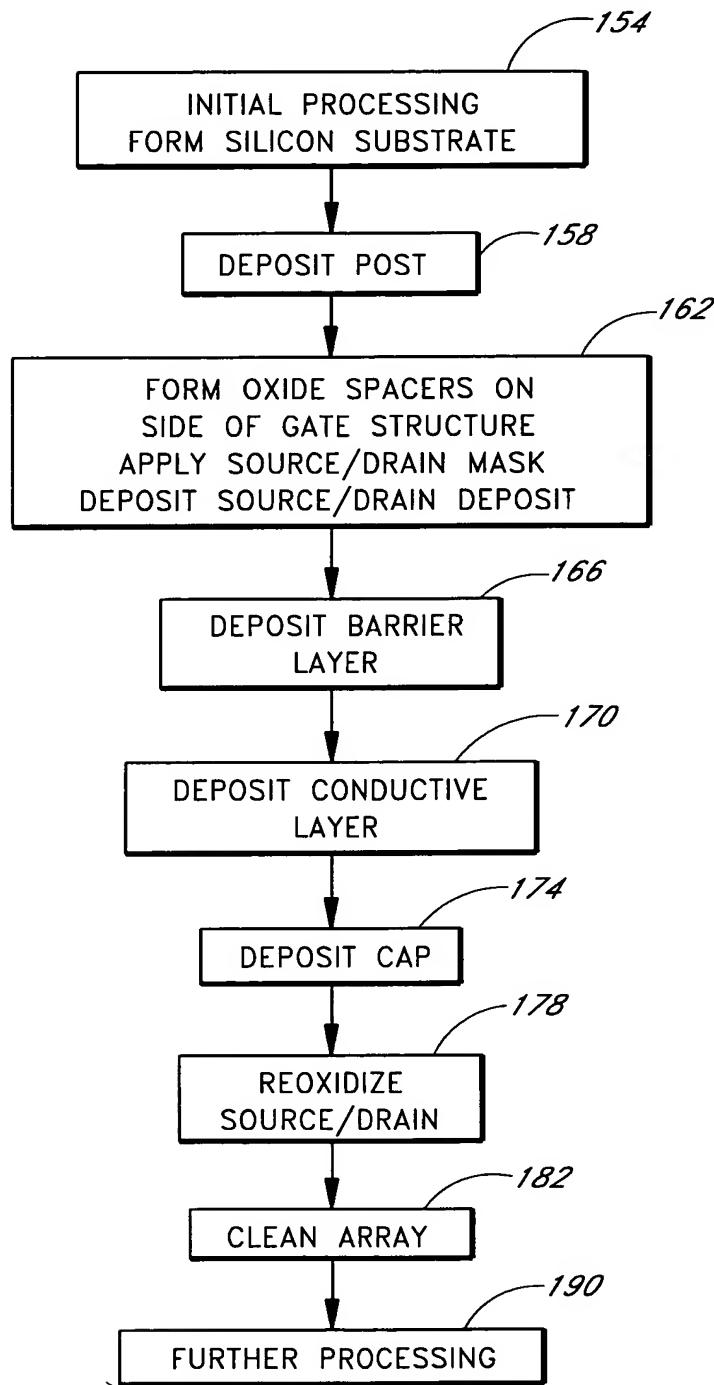


FIG. 7